74AHC573; 74AHCT573

Octal D-type transparant latch; 3-state Rev. 7 — 8 November 2011

Product data sheet

General description 1.

The 74AHC573; 74AHCT573 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7A.

The 74AHC573; 74AHCT573 consists of eight D-type transparent latches featuring separate D-type inputs for each latch and 3-state true outputs for bus oriented applications. A latch enable input (LE) and an output enable input (OE) are common to all latches.

When pin LE is HIGH, data at the Dn inputs enters the latches. In this condition the latches are transparent, i.e. a latch output will change state each time its corresponding Dn input changes. When pin LE is LOW, the latches store the information that is present at the Dn inputs, after a set-up time preceding the HIGH-to-LOW transition of LE.

When pin OE is LOW, the contents of the 8 latches are available at the outputs. When pin OE is HIGH, the outputs go to the high-impedance OFF-state. Operation of the OE input does not affect the state of the latches.

The 74AHC573; 74AHCT573 is functionally identical to the 74AHC373; 74AHCT373, but has a different pin arrangement.

2. **Features and benefits**

- Balanced propagation delays
- All inputs have a Schmitt trigger action
- Common 3-state output enable input
- Functionally identical to the 74AHC373; 74AHCT373
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - For 74AHC573: CMOS input level
 - ◆ For 74AHCT573: TTL input level
- ESD protection:
 - HBM EIA/JESD22-A114E exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
 - CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

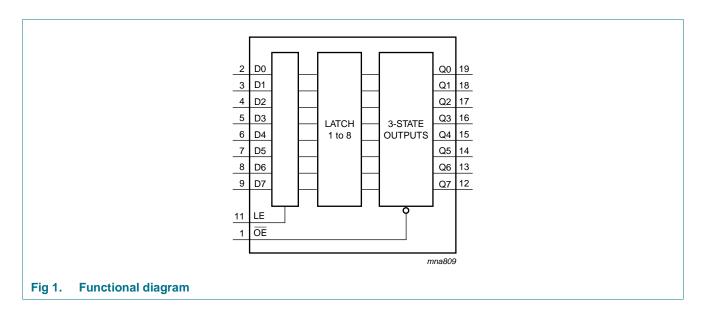


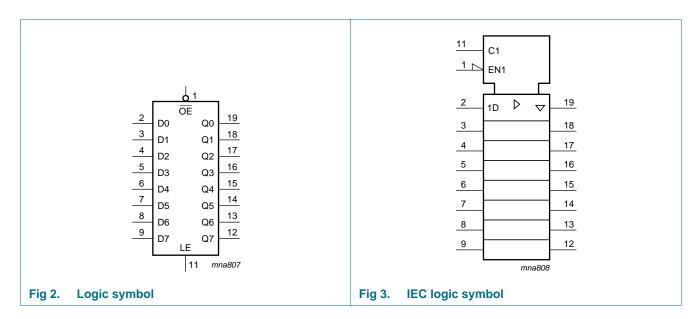
3. Ordering information

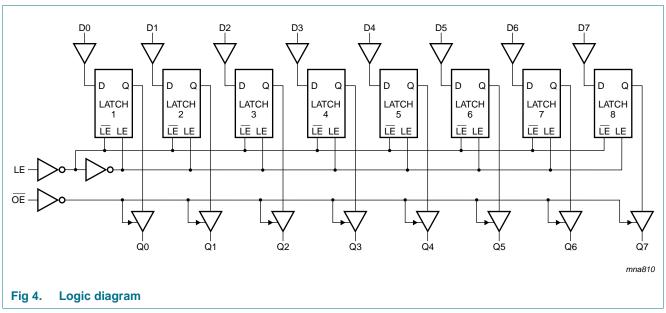
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC573				
74AHC573D	–40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC573PW	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHC573BQ	–40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package no leads; 20 terminals; body $2.5\times4.5\times0.85$ mm	SOT764-1
74AHCT573				
74AHCT573D	–40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-
74AHCT573PW	–40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-
74AHCT573BQ	–40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package no leads; 20 terminals; body $2.5\times4.5\times0.85$ mm	SOT764-

4. Functional diagram

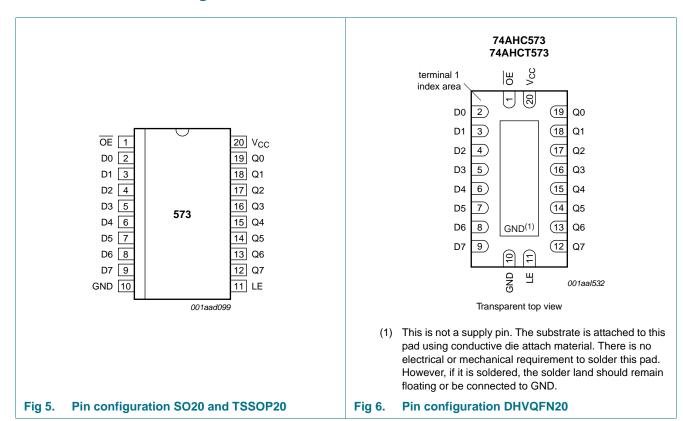






5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
ŌĒ	1	output enable input (active LOW)
D0 to D7	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
LE	11	latch enable (active HIGH)
Q0 to Q7	19, 18, 17, 16, 15, 14, 13, 12	data output
V _{CC}	20	supply voltage

6. Functional description

Table 3. Function table[1]

Operating mode	Input		Internal latch	Output	
	OE	LE	Dn		Qn
Enable and read register (transparent	L	Н	L	L	L
mode)			Н	Н	Н
Latch and read register	L	L	I	L	L
			h	Н	Н
Latch register and disable outputs	Н	L	I	L	Z
			h	Н	Z

^[1] H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the HIGH-to-LOW LE transition;

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 V$	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> –20	+20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-25	+25	mA
I _{CC}	supply current		-	+75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the HIGH-to-LOW LE transition;

Z = high-impedance OFF-state.

^[2] For SO20 packages: above 70 $^{\circ}$ C the value of P_{tot} derates linearly at 8 mW/K.

For TSSOP20 packages: above 60 $^{\circ}\text{C}$ the value of Ptot derates linearly at 5.5 mW/K.

For DHVQFN20 packages: above 60 $^{\circ}$ C the value of P_{tot} derates linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

	1 0					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHC573						
V _{CC}	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V
74AHCT573	3					
V _{CC}	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C			-40 °C to +85 °C		-40 °C to +125 °C		
			Min	Тур	Max	Min	Max	Min	Тур	Max	
74AHC5	73										
V_{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	-	1.65	V
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}									
	output voltage	$I_{O} = -50 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	-	V
		$I_{O} = -50 \mu A; V_{CC} = 3.0 V$	2.9	3.0	-	2.9	-	2.9	-	-	V
		$I_O = -50 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	-	V
		$I_O = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}									
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	-	0.55	V
		$I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	-	0.55	V

74AHC_AHCT573

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	to +85 °C	-40 °C to +125 °C			Unit
			Min	Тур	Max	Min	Max	Min	Тур	Max	1
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.25	-	±2.5	-	-	±10.0	μΑ
I ₁	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 0$ V to 5.5 V	-	-	0.1	-	1.0	-	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	-	80	μΑ
C _I	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	-	10	pF
Co	output capacitance		-	4	-	-	-	-	-	10	pF
74AHCT	573										
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	8.0	-	0.8	-	-	0.8	V
V _{OH} HIGH-level		$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$									
	output voltage	$I_{O} = -50 \mu A$	4.4	4.5	-	4.4	-	4.4	-	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$									
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	-	0.1	V
		$I_0 = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	-	0.55	V
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_O = 0$ A	-	-	±0.25	-	±2.5	-	-	±10.0	μА
I ₁	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	-	80	μΑ
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other pins at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	-	1.5	mA
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	-	10	pF
Co	output capacitance		-	4	-	-	-	-	-	10	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 11.

Symbol	Parameter	Conditions			25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC5	73				1			'		1	
t _{pd}	propagation	Dn to Qn; see Figure 7	[2]								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		$C_L = 15 pF$		-	5.5	11.0	1.0	13.0	1.0	14.0	ns
		$C_L = 50 pF$		-	7.8	14.5	1.0	16.5	1.0	18.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_L = 15 pF$		-	3.9	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50 pF$		-	5.5	8.8	1.0	10.0	1.0	11.0	ns
		LE to Qn; see Figure 8	[2]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		$C_L = 15 pF$		-	5.8	11.9	1.0	14.0	1.0	15.0	ns
		$C_L = 50 pF$		-	8.3	15.4	1.0	17.5	1.0	19.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_L = 15 pF$		-	4.2	7.7	1.0	9.0	1.0	10.0	ns
		$C_L = 50 pF$		-	5.9	9.7	1.0	11.0	1.0	12.5	ns
t _{en}	enable time	OE to Qn; see Figure 9	[3]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		$C_L = 15 pF$		-	5.8	11.5	1.0	13.5	1.0	14.5	ns
		$C_L = 50 pF$		-	8.3	15.0	1.0	17.0	1.0	19.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_L = 15 pF$		-	4.4	7.7	1.0	9.0	1.0	10.0	ns
		$C_L = 50 pF$		-	6.3	9.7	1.0	11.0	1.0	12.5	ns
t _{dis}	disable time	OE to Qn; see Figure 9	[4]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		$C_L = 15 pF$		-	6.8	11.0	1.0	13.0	1.0	14.0	ns
		$C_L = 50 pF$		-	9.7	14.5	1.0	16.5	1.0	18.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		$C_{L} = 15 \text{ pF}$		-	4.6	7.7	1.0	9.0	1.0	10.0	ns
		$C_L = 50 pF$		-	7.4	9.7	1.0	11.0	1.0	12.5	ns
t _W	pulse width	LE HIGH; see Figure 8									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	Dn to LE; see Figure 10									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		3.5	-	-	3.5	-	3.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		3.5	-	-	3.5	-	3.5	-	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 11.

Symbol	Parameter	Conditions			25 °C		-40 °C 1	to +85 °C	-40 °C t	Uni	
				Min	Typ[1]	Max	Min	Max	Min	Max	
t _h	hold time	Dn to LE; see Figure 10				•		1			'
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.5	-	-	1.5	-	1.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		1.5	-	-	1.5	-	1.5	-	ns
C_PD	power dissipation capacitance	$f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[5]</u>	-	12	-	-	-	-	-	pF
74AHCT	573; V _{CC} = 4.5	5 V to 5.5 V									
t _{pd}	propagation	Dn to Qn; see Figure 7	[2]								
	delay	C _L = 15 pF		-	3.5	5.5	1	6.5	1	7.0	ns
		$C_L = 50 pF$		-	4.9	7.5	1	8.5	1	9.5	ns
		LE to Qn; see Figure 8	[2]								
		C _L = 15 pF		-	3.9	6.0	1	7.0	1	7.5	ns
		$C_L = 50 pF$		-	5.5	8.5	1	9.5	1	11.0	ns
t _{en}	enable time	OE to Qn; see Figure 9	[3]								
		C _L = 15 pF		-	4.1	6.5	1	7.5	1	8.5	ns
		$C_L = 50 pF$		-	5.9	8.5	1	10.0	1	11.0	ns
t _{dis}	disable time	OE to Qn; see Figure 9	[4]								
		C _L = 15 pF		-	4.5	6.5	1	7.5	1	8.5	ns
		$C_L = 50 pF$		-	6.4	9.0	1	10.0	1	11.5	ns
t _W	pulse width	LE HIGH; see Figure 8		5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	Dn to LE; see Figure 10		3.5	-	-	3.5	-	3.5	-	ns
t _h	hold time	Dn to LE; see Figure 10		1.5	-	-	1.5	-	1.5	-	ns
C _{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC}	<u>[5]</u>	-	18	-	-	-	-	-	pF

^[1] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3 \text{ V}$ and $V_{CC} = 5.0 \text{ V}$).

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$$

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

^[2] t_{pd} is the same as t_{PHL} and t_{PLH} .

^[3] t_{en} is the same as t_{PZH} and t_{PZL} .

^[4] t_{dis} is the same as t_{PHZ} and t_{PLZ} .

11. Waveforms

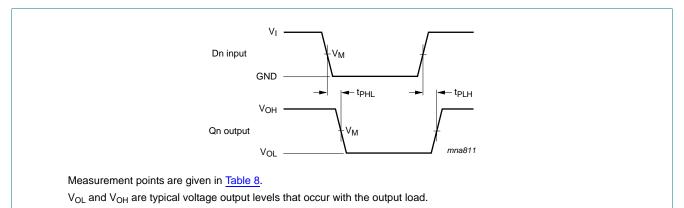
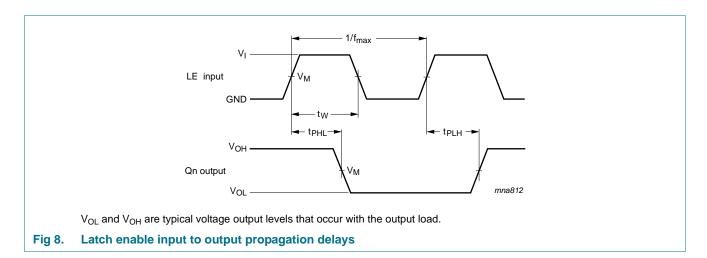
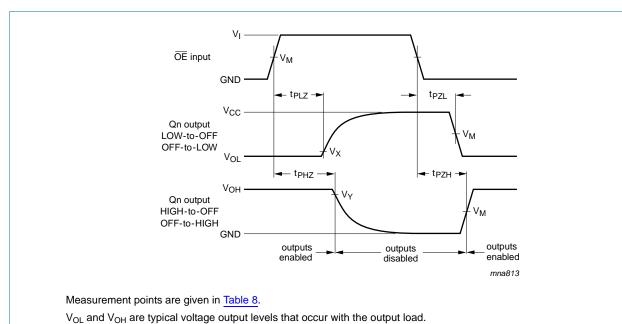


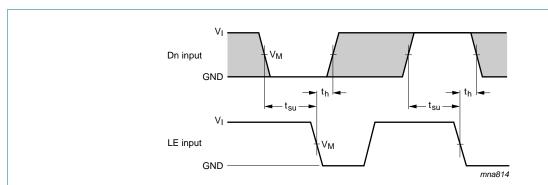
Fig 7. Data input to output propagation delays





9. Enable and disable times

Fig 9.



Measurement points are given in Table 8.

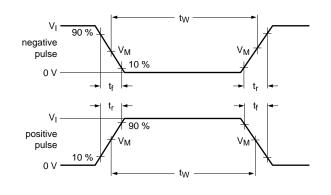
 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are typical voltage output levels that occur with the output load.

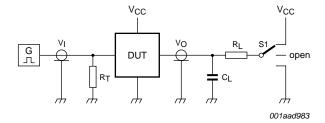
The shaded areas indicate when the input is permitted to change for predicable output performance.

Fig 10. Data set-up and hold times

Table 8. Measurement points

Туре	Input	Output						
	V _M	V _M	V _X	V _Y				
74AHC573	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$				
74AHCT573	1.5 V	$0.5 \times V_{CC}$	V _{OL} + 0.3 V	V _{OH} – 0.3 V				





Test data is given in Table 9.

Definitions test circuit:

 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = load capacitance including jig and probe capacitance.

R_L = load resistance.

S1 = test selection switch.

Fig 11. Test circuitry for switching times

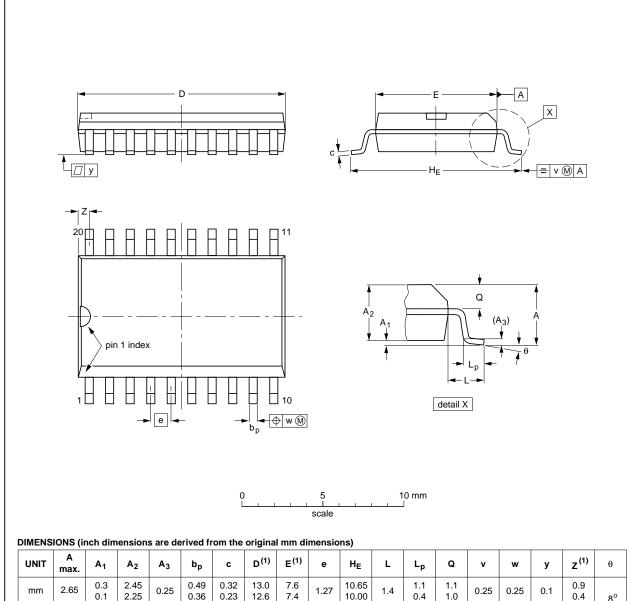
Table 9. Test data

Туре	Input		Load		S1 position			
	VI	t _r , t _f	CL	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
74AHC573	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	
74AHCT573	3.0 V	≤ 3.0 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	C	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	0°

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	IEC JEDEC				JEITA
SOT163-1	075E04	MS-013				99-12-27 03-02-19

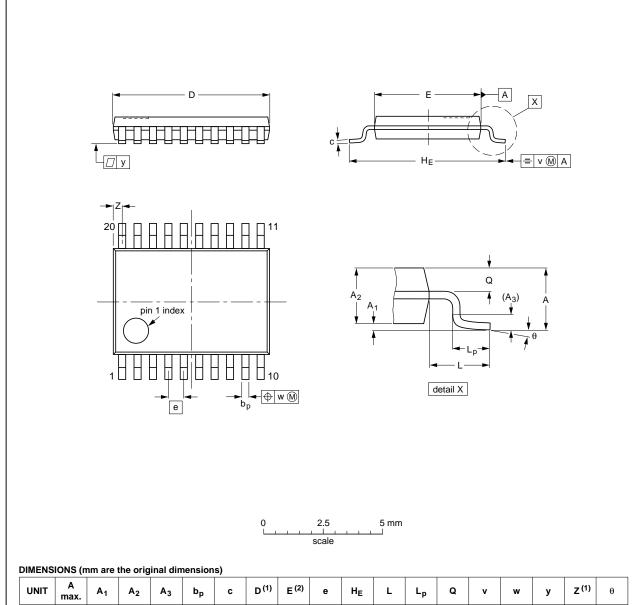
Fig 12. Package outline SOT163-1 (SO20)

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TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



Ξ							-,												
	UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE	
SOT360-1		MO-153				99-12-27 03-02-19	

Fig 13. Package outline SOT360-1 (TSSOP20)

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DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm SOT764-1

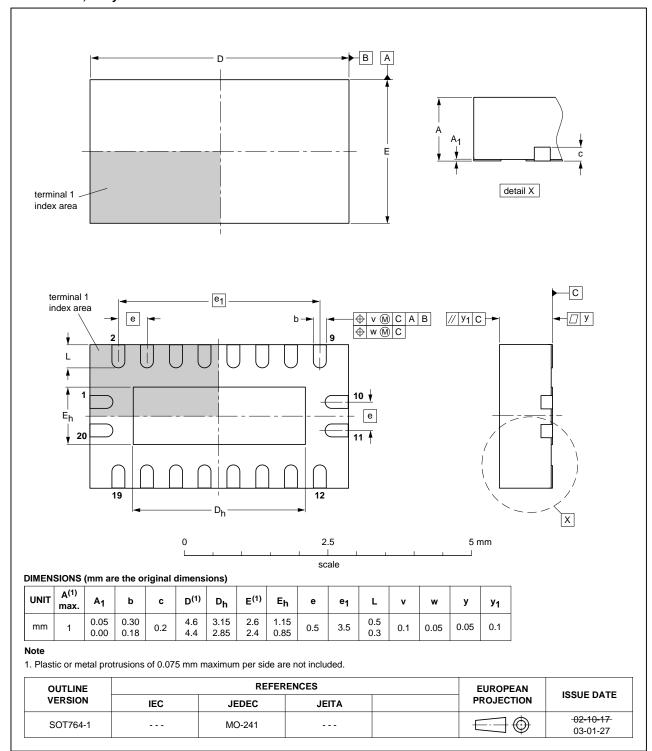


Fig 14. Package outline SOT764-1 (DHVQFN20)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

	,			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT573 v.7	20111108	Product data sheet	-	74AHC_AHCT573 v.6
Modifications:	 Legal pages 	s updated.		
74AHC_AHCT573 v.6	20101125	Product data sheet	-	74AHC_AHCT573 v.5
74AHC_AHCT573 v.5	20100325	Product data sheet	-	74AHC_AHCT573 v.4
74AHC_AHCT573 v.4	20100303	Product data sheet	-	74AHC_AHCT573 v.3
74AHC_AHCT573 v.3	20080424	Product data sheet	-	74AHC_AHCT573 v.2
74AHC_AHCT573 v.2	20031208	Product specification	-	74AHC_AHCT573 v.1
74AHC_AHCT573 v.1	19990927	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Octal D-type transparant latch; 3-state

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